

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1325	(phase adj change) with CELL	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 17:21
L2	141	(phase adj change) with cell and tellurium	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 15:37
L3	19	(phase adj change) with cell with tellurium	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 15:46
L4	0	(phase adj change chalcogen\$3) with tellurium with (eletrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 15:46
L5	41	((phase adj change chalcogen\$3) with tellurium) with (electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 16:00
L6	396	((phase adj change chalcogen\$3) with ("Te" tellurium)) with (cell memory)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 16:01
L7	298	((phase adj change chalcogen\$3) near5 ("Te" tellurium)) with (cell memory)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 16:01
L8	4	((phase adj change chalcogen\$3) near5 ("Te" tellurium)) with (cell memory) with (trench hole via recess damascene)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 16:03
L9	20	((phase adj change chalcogen\$3) near5 ("Te" tellurium)) with (trench hole via recess damascene)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 16:03
L10	4760	(phase near3 change\$3 chalcogenide chalcogen ovonic) with (recess trench hole via groove opening pore damascene)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 16:06
L11	219	(phase near3 change\$3 chalcogenide chalcogen ovonic) with (recess trench hole via groove opening pore damascene) with ("Te" tellurium)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 16:09
L12	3	(phase near3 change\$3 chalcogenide chalcogen ovonic) with (recess trench hole via groove opening pore damascene) with ("Te" tellurium) with electrode	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 16:09
L13	219	11 and (phase near3 change\$3 chalcogenide chalcogen ovonic) with ("Te" tellurium)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 17:26

EAST Search History

L14	180	(phase adj change) with pore	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 17:21
L15	3	(phase adj change) with pore with ("Te" tellurium)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 17:23
L16	200	(phase near3 change\$3 chalcogenide chalcogen ovonic) with ("Te" tellurium) with (trench via hole groove damascene recess depression)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 17:35
L17	3915	(phase near3 change\$3 chalcogenide chalcogen ovonic) with (trench via hole groove damascene recess depression)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 17:35
L18	661	17 and (phase near3 change\$3 chalcogenide chalcogen ovonic) with ("Te" tellurium)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 17:36
L19	386	17 and (phase near3 change\$3 chalcogenide chalcogen ovonic) near5("Te" tellurium)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 17:36
L20	179	19 and (phase near3 change\$3 chalcogenide chalcogen ovonic "Te" tellurium) with (conduct\$3 electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 18:00
L21	2	10/787121	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 18:00
L22	1	21 and "Te"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 18:05
L23	1	"6921912"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 18:05
L24	3	09/740256	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 18:25
L25	2	09/803176	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 18:25
S32	185	(phase adj change) with capacitor	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 15:36
S33	1482	(phase adj change) with memory	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:16

EAST Search History

S35	1661	S32 or S33	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:16
S36	1661	S35 and (phase adj change capacitor memory)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:23
S37	416	"22" and ((phase adj change) with electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:19
S38	182	S36 and ((phase adj change) with electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:19
S39	121	S38 and ((recess trench hole via groove opening) with electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:21
S40	131	S38 and ((recess trench hole via groove opening pore damascene) with electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:23
S41	2081	438/259,270.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:22
S42	0	S41 and S36	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:22
S43	592	S41 and (phase adj change capacitor memory)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:23
S44	246	S43 and ((recess trench hole via groove opening pore damascene) with electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:58
S45	2	S43 and (phase adj change)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 14:59
S46	0	S41 and ((phase adj change) with (memory capaitor material layer))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 15:00
S47	10493	((phase adj change) with (memory capaitor material layer))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 15:01
S48	40	((phase adj change) with (memory capaitor material layer)) with (electrode near5 (recess trench pore damascene hole opening groove aperture))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/11/24 15:03
S49	2161	(phase adj change) with (capacitor memory)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:18

EAST Search History

S50	3110	(phase near3 change) with (capacitor memory)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:19
S51	3869	(phase near3 change\$3 chalcogenide ovonic) with (capacitor memory)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:24
S52	433445	(recess trench hole via groove opening pore damascene) with (electrode plug pillar column)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:28
S53	4213	(phase near3 change\$3 chalcogenide ovonic) with (recess trench hole via groove opening pore damascene)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/03/29 16:05
S54	1960	(phase near3 change\$3 chalcogenide ovonic) near5 (recess trench hole via groove opening pore damascene)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:26
S55	424	S51 and (phase near3 change\$3 chalcogenide ovonic) near5 (recess trench hole via groove opening pore damascene)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:28
S56	279	S55 and S52	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:27
S57	279	S56 and (phase near3 change\$3 chalcogenide ovonic recess trench hole via groove opening pore damascene)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:28
S58	279	S57 and (recess trench hole via groove opening pore damascene electrode plug pillar column)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/09/09 13:28